

MOSPEC

HORIZONTAL DEFLECTION POWER TRANSISTORS

...specifically designed for use in color TV deflection circuits.

FEATURES:

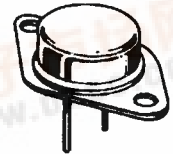
- * High Voltage: $V_{CES}=1500V$
- * Low Saturation Voltage: $V_{CE(sat)}=5.0V(Max.) @ I_C = 1.0 A$
- * High Speed: $t_r=1.0 us(Max.) @ I_{CP}=0.8 A, I_{B1} = 0.16A$
- * Built-in Damper Type
- * Glass Passivated Collector-Base Junction

NPN
2SD897A

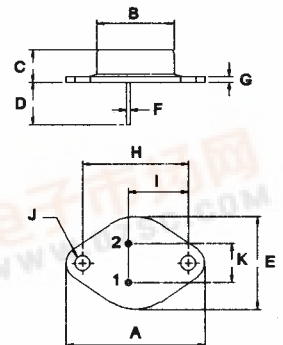
1.5 AMPERE
POWER
TRANSISTORS
1500 VOLTS
50 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CES}	1500	V
Collector-Emitter Voltage	V_{CEO}	600	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current-Continuous -Peak	I_C I_{CM}	1.5 5.0	A
Base Current	I_B	0.8	A
Total Power Dissipation @ $T_C=25^\circ C$ Derate above $25^\circ C$	P_D	50 0.4	W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +150	$^\circ C$



TO-3

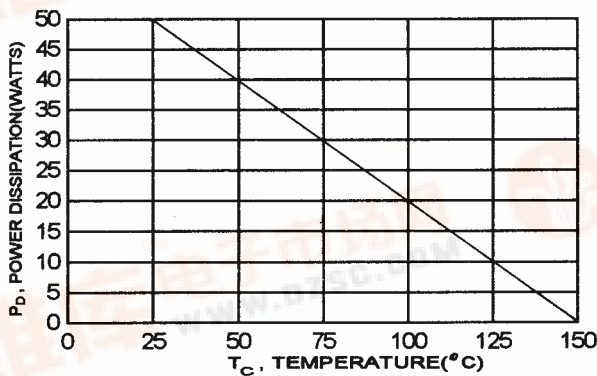


PIN 1.BASE
2.EMITTER
COLLECTOR(CASE)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	2.5	$^\circ C/W$

FIGURE -1 POWER DERATING



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector Cutoff Current ($V_{CE}=1500\text{ V}$, $R_{BE}=0$)	I_{CES}		500	μA
Emitter-Base Voltage ($I_E = 200\text{ mA}$, $I_C = 0$)	V_{EBO}	6.0		V

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 0.5\text{ A}$, $V_{CE} = 5.0\text{ V}$)	hFE	8.0		
Collector - Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 0.2\text{ A}$)	$V_{CE(sat)}$		5.0	V
Base - Emitter Saturation Voltage ($I_C = 1.0\text{ A}$, $I_B = 0.2\text{ A}$)	$V_{BE(sat)}$		1.5	V
Forward Voltage (Damper Diode) ($I_F = 2.0\text{ A}$)	$-V_F$		2.5	V

DYNAMIC CHARACTERISTICS

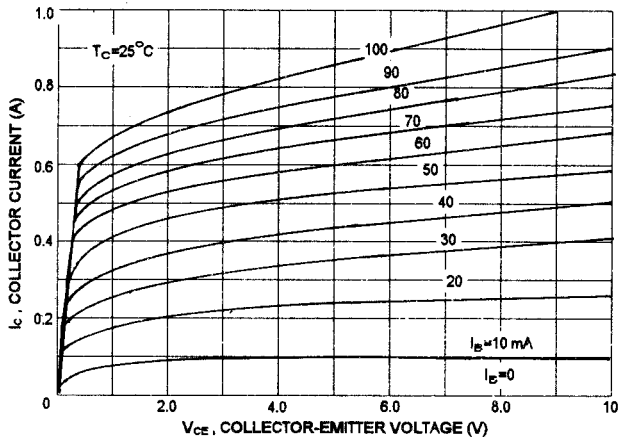
Current Gain - Bandwidth Product ($I_C = 0.1\text{ A}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	f_T	3.0(typ)		MHz
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SWITCHING CHARACTERISTICS

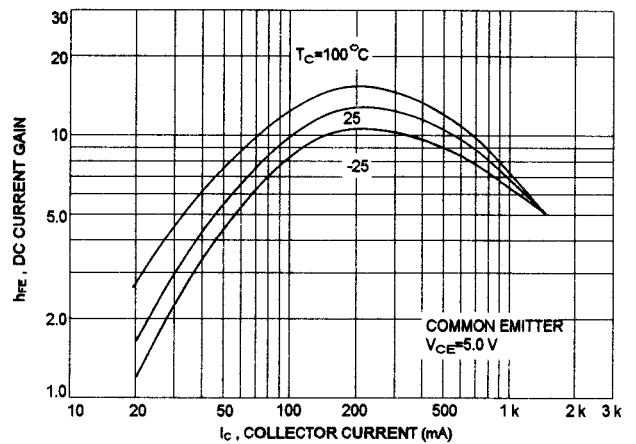
Fall Time	$I_C = 0.8\text{ A}$, $I_{B1(\text{end})} = 0.16\text{ A}$	t_f	1.0	μs
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(1) Pulse Test: Pulse width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

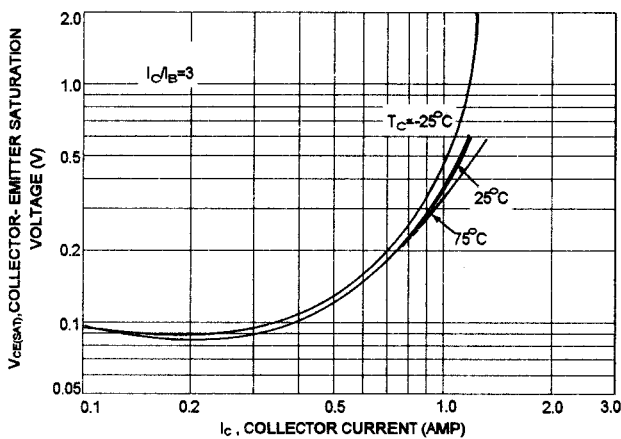
$I_c - V_{ce}$



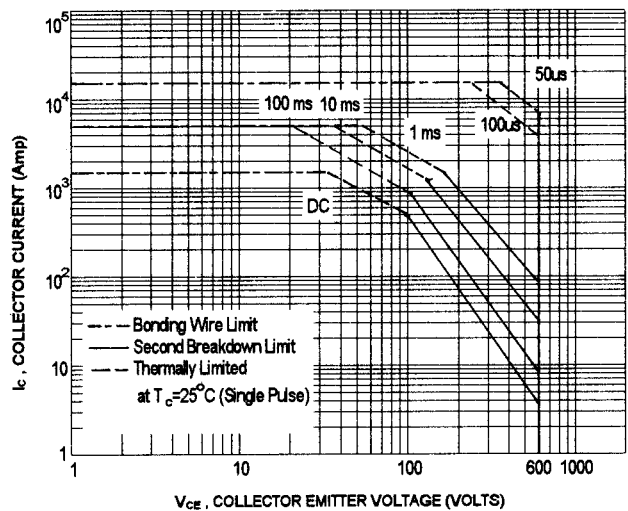
DC CURRENT GAIN



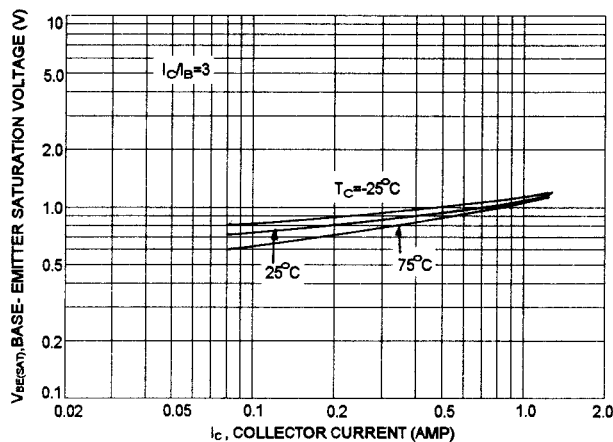
$V_{ce(sat)} - I_c$



ACTIVE-REGION SAFE OPERATING AREA (SOA)



$V_{be(sat)} - I_c$



There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate $I_c - V_{ce}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{j(pk)} = 150^\circ C$; T_c is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{j(pk)} \leq 150^\circ C$. At high case temperatures, thermal limita - tion will reduce the power that can be handled to values less than the limitations imposed by second breakdown.